



## 512Kx16 SRAM MODULE

ADVANCED\*

### FEATURES

- Access Times 17, 20, 25, 35ns
- MIL-STD-883 Compliant Devices Available
- Packaging
  - 44 pin Ceramic SOJ (Package 102)
  - 44 lead Ceramic Flatpack (Package 209)
- Organized as two banks of 256Kx16
- Data Byte Control:
  - Lower Byte ( $\overline{\text{LB}}$ ) = I/O<sub>1-8</sub>
  - Upper Byte ( $\overline{\text{UB}}$ ) = I/O<sub>9-16</sub>

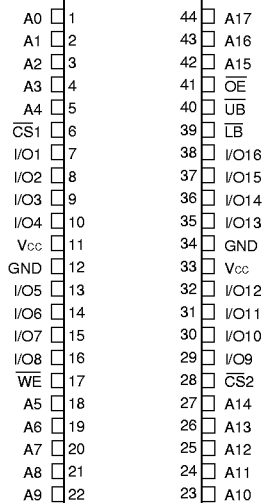
- Data I/O Compatible with 3.3V devices
- 2V Minimum Data Retention for battery back up operation
- Commercial, Industrial and Military Temperature Range
- 5 Volt Power Supply (3.3V parts also available)
- Low Power CMOS
- TTL Compatible Inputs and Outputs

\* This data sheet describes a product that may or may not be under development and is subject to change or cancellation without notice.

### PIN CONFIGURATION FOR WS512K16-XXX

#### 44 CSOJ 44 FLATPACK

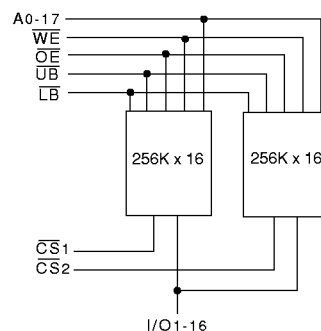
##### TOP VIEW



### PIN DESCRIPTION

| A0-17                        | Address Inputs                            |
|------------------------------|-------------------------------------------|
| $\overline{\text{LB}}$       | Lower-Byte Control (I/O <sub>1-8</sub> )  |
| $\overline{\text{UB}}$       | Upper-Byte Control (I/O <sub>9-16</sub> ) |
| I/O <sub>1-16</sub>          | Data Input/Output                         |
| $\overline{\text{CS}}_{1-2}$ | Chip Select                               |
| $\overline{\text{OE}}$       | Output Enable                             |
| $\overline{\text{WE}}$       | Write Enable                              |
| V <sub>cc</sub>              | +5.0V Power                               |
| GND                          | Ground                                    |
| NC                           | No Connection                             |

### BLOCK DIAGRAM





## TRUTH TABLE

| $\overline{CS}_1$ | $\overline{CS}_2$ | $\overline{WE}$ | $\overline{OE}$ | $\overline{LB}$ | $\overline{UB}$ | Mode           | Data I/O           |                     | Power   |
|-------------------|-------------------|-----------------|-----------------|-----------------|-----------------|----------------|--------------------|---------------------|---------|
|                   |                   |                 |                 |                 |                 |                | I/O <sub>1-8</sub> | I/O <sub>9-16</sub> |         |
| H                 | H                 | X               | X               | X               | X               | Not Select     | High Z             | High Z              | Standby |
| L                 | H                 | H               | H               | X               | X               | Output Disable | High Z             | High Z              | Active  |
| H                 | L                 |                 |                 |                 |                 |                |                    |                     |         |
| L                 | H                 | X               | X               | H               | H               |                |                    |                     |         |
| H                 | L                 |                 |                 |                 |                 |                |                    |                     |         |
| H                 | L                 | H               | L               | L               | H               | Read           | Data Out           | High Z              | Active  |
| L                 | H                 |                 |                 | H               | L               |                | High Z             | Data Out            |         |
| L                 | H                 |                 |                 | L               | L               |                | Data Out           | Data Out            |         |
| H                 | L                 | L               | X               | L               | H               | Write          | Data In            | High Z              | Active  |
| L                 | H                 |                 |                 | H               | L               |                | High Z             | Data In             |         |
| L                 | H                 |                 |                 | L               | L               |                | Data In            | Data In             |         |

## ABSOLUTE MAXIMUM RATINGS

| Parameter                      | Symbol           | Min  | Max                  | Unit |
|--------------------------------|------------------|------|----------------------|------|
| Operating Temperature          | T <sub>A</sub>   | -55  | +125                 | °C   |
| Storage Temperature            | T <sub>STG</sub> | -65  | +150                 | °C   |
| Signal Voltage Relative to GND | V <sub>G</sub>   | -0.5 | V <sub>CC</sub> +0.5 | V    |
| Junction Temperature           | T <sub>J</sub>   |      | 150                  | °C   |
| Supply Voltage                 | V <sub>CC</sub>  | -0.5 | 7.0                  | V    |

## RECOMMENDED OPERATING CONDITIONS

| Parameter              | Symbol          | Min  | Max                   | Unit |
|------------------------|-----------------|------|-----------------------|------|
| Supply Voltage         | V <sub>CC</sub> | 4.5  | 5.5                   | V    |
| Input High Voltage     | V <sub>IH</sub> | 2.2  | V <sub>CC</sub> + 0.3 | V    |
| Input Low Voltage      | V <sub>IL</sub> | -0.3 | +0.8                  | V    |
| Operating Temp. (Mil.) | T <sub>A</sub>  | -55  | +125                  | °C   |

## CAPACITANCE

(T<sub>A</sub> = +25°C)

| Parameter          | Symbol           | Condition                         | Max | Unit |
|--------------------|------------------|-----------------------------------|-----|------|
| Input capacitance  | C <sub>IN</sub>  | V <sub>IN</sub> = 0V, f = 1.0MHz  | 25  | pF   |
| Output capacitance | C <sub>OUT</sub> | V <sub>OUT</sub> = 0V, f = 1.0MHz | 25  | pF   |

This parameter is guaranteed by design but not tested.

## DC CHARACTERISTICS

(V<sub>CC</sub> = 5.0V, GND = 0V, T<sub>A</sub> = -55°C to +125°C)

| Parameter                | Sym             | Conditions                                                                                                        | MinMax |     | Units |
|--------------------------|-----------------|-------------------------------------------------------------------------------------------------------------------|--------|-----|-------|
| Input Leakage Current    | I <sub>LI</sub> | V <sub>CC</sub> = 5.5, V <sub>IN</sub> = GND to V <sub>CC</sub>                                                   |        | 10  | μA    |
| Output Leakage Current   | I <sub>LO</sub> | $\overline{CS}$ = V <sub>IH</sub> , $\overline{OE}$ = V <sub>IH</sub> , V <sub>OUT</sub> = GND to V <sub>CC</sub> |        | 10  | μA    |
| Operating Supply Current | I <sub>CC</sub> | $\overline{CS}$ = V <sub>IL</sub> , $\overline{OE}$ = V <sub>IH</sub> , f = 5MHz, V <sub>CC</sub> = 5.5           |        | 290 | m A   |
| Standby Current          | I <sub>SB</sub> | $\overline{CS}$ = V <sub>IH</sub> , $\overline{OE}$ = V <sub>IH</sub> , f = 5MHz, V <sub>CC</sub> = 5.5           |        | 30  | mA    |
| Output Low Voltage       | V <sub>OL</sub> | I <sub>OL</sub> = 8mA, V <sub>CC</sub> = 4.5                                                                      |        | 0.4 | V     |
| Output High Voltage      | V <sub>OH</sub> | I <sub>OH</sub> = -4.0mA, V <sub>CC</sub> = 4.5                                                                   | 2.4    |     | V     |

NOTE: DC test conditions: V<sub>IH</sub> = V<sub>CC</sub> - 0.3V, V<sub>IL</sub> = 0.3V

## DATA RETENTION CHARACTERISTICS

(T<sub>A</sub> = -55°C to +125°C)

| Parameter                     | Symbol             | Conditions                         |     |     |       | Units |
|-------------------------------|--------------------|------------------------------------|-----|-----|-------|-------|
|                               |                    |                                    | Min | Typ | Max   |       |
| Data Retention Supply Voltage | V <sub>DR</sub>    | $\overline{CS} \geq V_{CC} - 0.2V$ | 2.0 |     | 5.5   | V     |
| Data Retention Current        | I <sub>CCDR1</sub> | V <sub>CC</sub> = 3V               |     | 2.0 | 12.0* | mA    |

\* Also available in Low Power version. Please call factory for information.



## AC CHARACTERISTICS

(V<sub>CC</sub> = 5.0V, GND = 0V, T<sub>A</sub> = -55°C to +125°C)

| Parameter                                                                | Symbol                        | -17 |     | -20 |     | -25 |     | -35 |     | Units |
|--------------------------------------------------------------------------|-------------------------------|-----|-----|-----|-----|-----|-----|-----|-----|-------|
|                                                                          |                               | Min | Max | Min | Max | Min | Max | Min | Max |       |
| Read Cycle Time                                                          | t <sub>RC</sub>               | 17  |     | 20  |     | 25  |     | 35  |     | ns    |
| Address Access Time                                                      | t <sub>AA</sub>               |     | 17  |     | 20  |     | 25  |     | 35  | ns    |
| Output Hold from Address Change                                          | t <sub>OH</sub>               | 0   |     | 0   |     | 0   |     | 0   |     | ns    |
| Chip Select Access Time                                                  | t <sub>ACS</sub>              |     | 17  |     | 20  |     | 25  |     | 35  | ns    |
| Output Enable to Output Valid                                            | t <sub>OE</sub>               |     | 10  |     | 12  |     | 15  |     | 20  | ns    |
| Chip Select to Output in Low Z                                           | t <sub>CLZ</sub> <sup>1</sup> | 2   |     | 5   |     | 5   |     | 5   |     | ns    |
| Output Enable to Output in Low Z                                         | t <sub>OLZ</sub> <sup>1</sup> | 0   |     | 0   |     | 0   |     | 0   |     | ns    |
| Chip Disable to Output in High Z                                         | t <sub>CHZ</sub> <sup>1</sup> |     | 9   |     | 10  |     | 12  |     | 15  | ns    |
| Output Disable to Output in High Z                                       | t <sub>OHZ</sub> <sup>1</sup> |     | 9   |     | 10  |     | 12  |     | 15  | ns    |
| $\overline{\text{LB}}$ , $\overline{\text{UB}}$ Access Time              | t <sub>BA</sub>               |     | 10  |     | 12  |     | 14  |     | 17  | ns    |
| $\overline{\text{LB}}$ , $\overline{\text{UB}}$ Enable to Low Z Output   | t <sub>BLZ</sub> <sup>1</sup> | 0   |     | 0   |     | 0   |     | 0   |     | ns    |
| $\overline{\text{LB}}$ , $\overline{\text{UB}}$ Disable to High Z Output | t <sub>BHZ</sub> <sup>1</sup> |     | 9   |     | 10  |     | 12  |     | 15  | ns    |

1. This parameter is guaranteed by design but not tested.

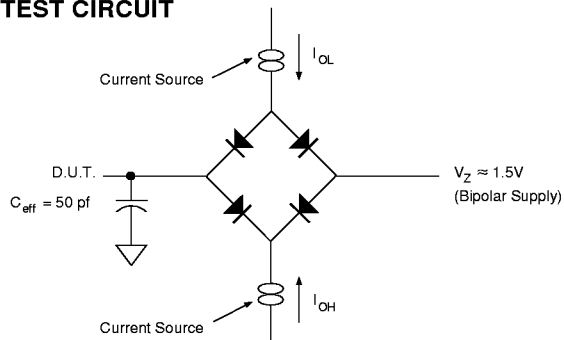
## AC CHARACTERISTICS

(V<sub>CC</sub> = 5.0V, GND = 0V, T<sub>A</sub> = -55°C to +125°C)

| Parameter                                                             | Symbol                        | -17 |     | -20 |     | -25 |     | -35 |     | Units |
|-----------------------------------------------------------------------|-------------------------------|-----|-----|-----|-----|-----|-----|-----|-----|-------|
|                                                                       |                               | Min | Max | Min | Max | Min | Max | Min | Max |       |
| Write Cycle Time                                                      | t <sub>WC</sub>               | 17  |     | 20  |     | 25  |     | 35  |     | ns    |
| Chip Select to End of Write                                           | t <sub>CW</sub>               | 14  |     | 17  |     | 20  |     | 25  |     | ns    |
| Address Valid to End of Write                                         | t <sub>AW</sub>               | 14  |     | 17  |     | 20  |     | 25  |     | ns    |
| Data Valid to End of Write                                            | t <sub>DW</sub>               | 10  |     | 12  |     | 15  |     | 20  |     | ns    |
| Write Pulse Width                                                     | t <sub>WP</sub>               | 14  |     | 17  |     | 20  |     | 25  |     | ns    |
| Address Setup Time                                                    | t <sub>AS</sub>               | 0   |     | 0   |     | 0   |     | 0   |     | ns    |
| Address Hold Time                                                     | t <sub>AH</sub>               | 0   |     | 0   |     | 0   |     | 0   |     | ns    |
| Output Active from End of Write                                       | t <sub>OW</sub> <sup>1</sup>  | 0   |     | 0   |     | 0   |     | 0   |     | ns    |
| Write Enable to Output in High Z                                      | t <sub>WHZ</sub> <sup>1</sup> |     | 9   |     | 10  |     | 10  |     | 15  | ns    |
| Data Hold Time                                                        | t <sub>DH</sub>               | 0   |     | 0   |     | 0   |     | 0   |     | ns    |
| $\overline{\text{LB}}$ , $\overline{\text{UB}}$ Valid to End of Write | t <sub>BW</sub>               | 14  |     | 17  |     | 20  |     | 25  |     | ns    |

1. This parameter is guaranteed by design but not tested.

### AC TEST CIRCUIT

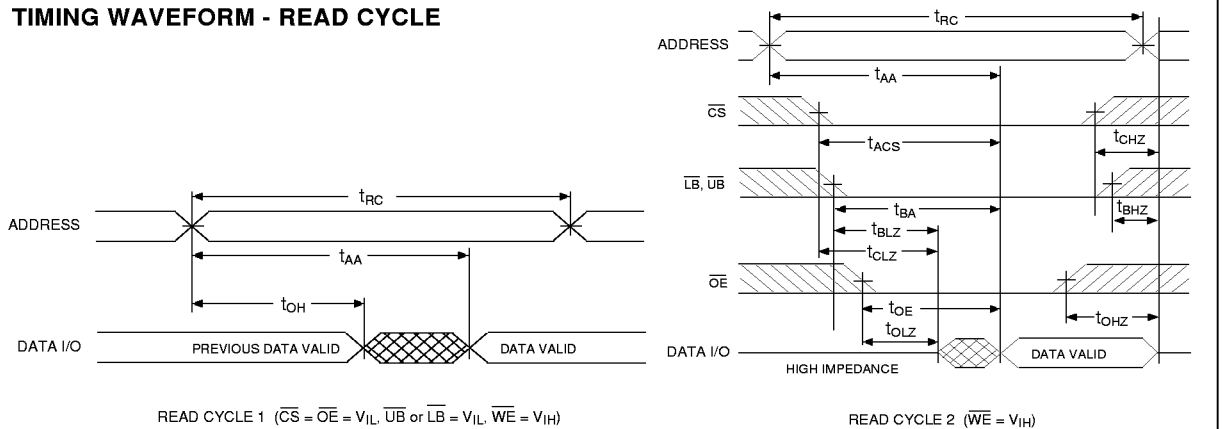
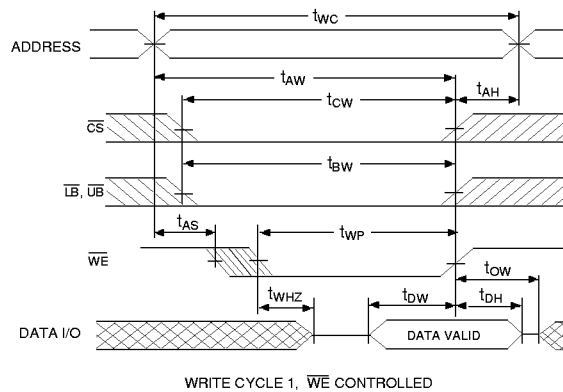
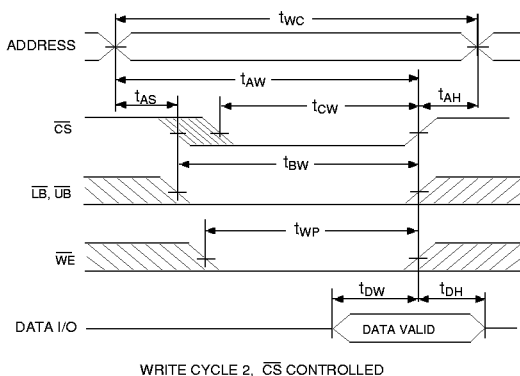
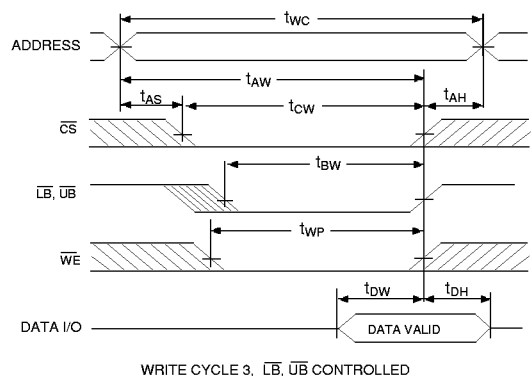


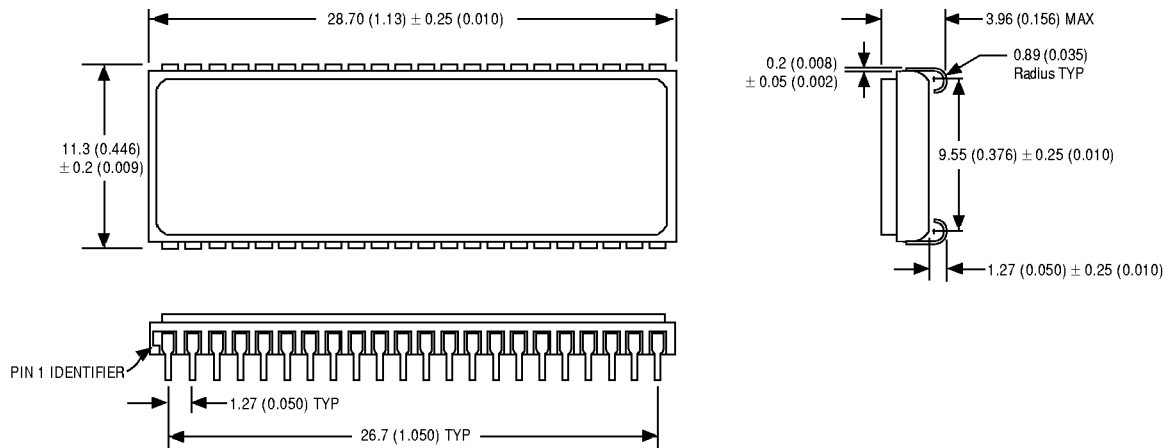
### AC TEST CONDITIONS

| Parameter                        | Typ                                        | Unit |
|----------------------------------|--------------------------------------------|------|
| Input Pulse Levels               | V <sub>IL</sub> = 0, V <sub>IH</sub> = 3.0 | V    |
| Input Rise and Fall              | 5                                          | ns   |
| Input and Output Reference Level | 1.5                                        | V    |
| Output Timing Reference Level    | 1.5                                        | V    |

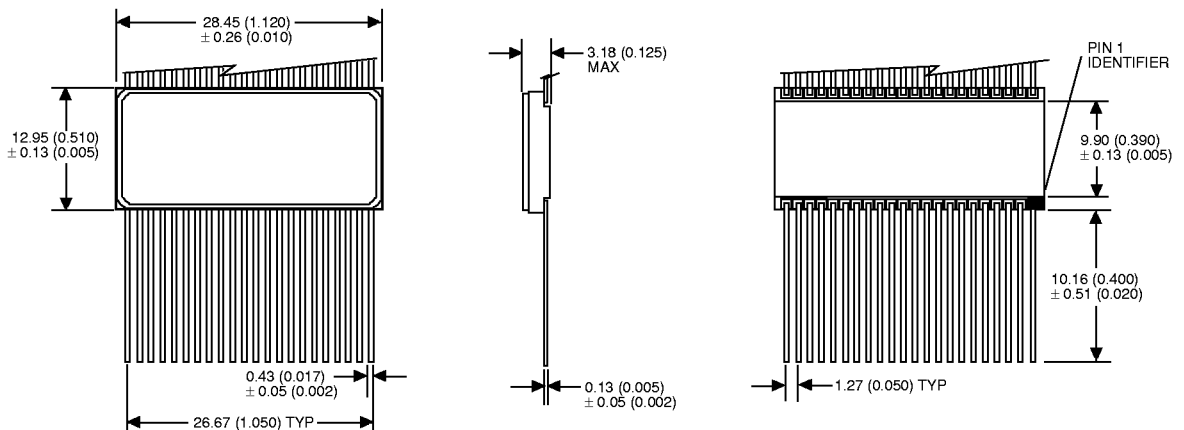
#### NOTES:

V<sub>Z</sub> is programmable from -2V to +7V.  
 $I_{OL}$  &  $I_{OH}$  programmable from 0 to 16mA.  
 Tester Impedance Z<sub>0</sub> = 75 Ω.  
 V<sub>Z</sub> is typically the midpoint of V<sub>OH</sub> and V<sub>OL</sub>.  
 $I_{OL}$  &  $I_{OH}$  are adjusted to simulate a typical resistive load circuit.  
 ATE tester includes jig capacitance.

**TIMING WAVEFORM - READ CYCLE****WRITE CYCLE -  $\overline{WE}$  CONTROLLED****WRITE CYCLE -  $\overline{CS}$  CONTROLLED****WRITE CYCLE -  $\overline{LB}$ ,  $\overline{UB}$  CONTROLLED**

**PACKAGE 102: 44 LEAD, CERAMIC SOJ**

ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

**PACKAGE 209: 44 LEAD, CERAMIC FLAT PACK**

ALL LINEAR DIMENSIONS ARE MILLIMETERS AND PARENTHETICALLY IN INCHES

**ORDERING INFORMATION****W S 512K16 - XX X X X****LEAD FINISH:**

Blank = Gold plated leads

A = Solder dip leads

**DEVICE GRADE:**

M = Military Screened -55°C to +125°C

I = Industrial -40°C to +85°C

C = Commercial 0°C to +70°C

**PACKAGE:**

DL = 44 Lead Ceramic SOJ (Package 102)

FL = 44 Lead Ceramic Flatpack (Package 209)

**ACCESS TIME (ns)****ORGANIZATION, two banks of 256K x 16****SRAM****WHITE MICROELECTRONICS**